MOSFET - Power, N-Channel, SUPERFET® III, FRFET®

650 V, 65 A, 40 mΩ

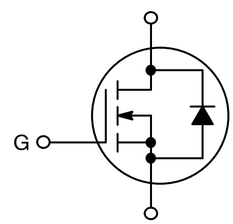
Product Preview

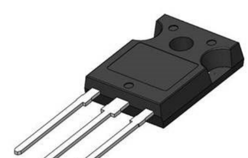
NVHL040N65S3HF

ON Semiconductor®

www.onsemi.com

V_{DSS}	$R_{DS(ON)}$ MAX	I_D MAX
650 V	40 mΩ @ 10 V	65 A





TO−247 Long Leads
CASE 340CX

Description

SUPERFET III MOSFET is ON Semiconductor's brand−new high voltage super−junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate.

Consequently, SUPERFET III MOSFET is very suitable for the various power system for miniaturization and higher efficiency.

SUPERFET III HF version provides fast recovery for improved efficiency in high speed switching applications.

Features

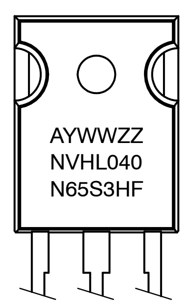
- 700 V @ T_J = 150°C
- Typ. $R_{DS(on)}$ = 31 mΩ
- Ultra Low Gate Charge (Typ. Q_g = 157 nC)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)}$ = 1374 pF)
- 100% Avalanche Tested
- NVHL Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Automotive On Board Charger HEV−EV
- Automotive DC/DC Converter for HEV−EV

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.

MARKING DIAGRAM



A = Assembly Plant Code
YWW = Data Code (Year & Week)
ZZ = Assembly Lot Code
NVHL040N65S3HF = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, Unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{DSS}	Drain to Source Voltage		650	V
V_{GSS}	Gate to Source Voltage	– DC	±30	V
		– AC (f > 1 Hz)	±30	
I_D	Drain Current	– Continuous (T_C = 25°C)	65	A
		– Continuous (T_C = 100°C)	45	
I_{DM}	Drain Current	– Pulsed (Note 1)	162.5	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		1009	mJ
I_{AS}	Avalanche Current (Note 2)		9	A
E_{AR}	Repetitive Avalanche Energy (Note 1)		4.46	mJ
dv/dt	MOSFET dv/dt		100	V/ns
	Peak Diode Recovery dv/dt (Note 3)		50	
P_D	Power Dissipation	(T_C = 25°C)	446	W
		– Derate Above 25°C	3.57	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		−55 to +150	°C
T_L	Maximum Lead Temperature for Soldering, 1/8″ from Case for 5 seconds		300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse−width limited by maximum junction temperature.
2. I_{AS} = 9 A, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 32.5 A, di/dt ≤ 200 A/μs, V_{DD} ≤ 400 V, starting T_J = 25°C.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.28	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
NVHL040N65S3HF	NVHL040N65S3HF	TO−247	Tube	N/A	N/A	30 Units

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain to Source Breakdown Voltage	V_{GS} = 0 V, I_D = 1 mA, T_J = 25°C	650			V
		V_{GS} = 0 V, I_D = 1 mA, T_J = 150°C	700			V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	I_D = 15 mA, Referenced to 25°C		0.63		V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 650 V, V_{GS} = 0 V			10	μA
		V_{DS} = 520 V, T_C = 125°C		28		
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±30 V, V_{DS} = 0 V			±100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 2.1 mA	3.0		5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 32.5 A		31	40	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 20 V, I_D = 32.5 A		45		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 400 V, V_{GS} = 0 V, f = 1 MHz		6655		pF
C_{oss}	Output Capacitance			143		pF
$C_{oss(eff.)}$	Effective Output Capacitance	V_{DS} = 0 V to 400 V, V_{GS} = 0 V		1374		pF
$C_{oss(er.)}$	Energy Related Output Capacitance	V_{DS} = 0 V to 400 V, V_{GS} = 0 V		250		pF
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{DS} = 400 V, I_D = 32.5 A, V_{GS} = 10 V (Note 4)		157		nC
Q_{gs}	Gate to Source Gate Charge			49		nC
Q_{gd}	Gate to Drain “Miller” Charge			61		nC
ESR	Equivalent Series Resistance	f = 1 MHz		1.1		Ω
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 400 V, I_D = 32.5 A, V_{GS} = 10 V, R_g = 2.2 Ω (Note 4)		42.2		ns
t_r	Turn-On Rise Time			27.4		ns
$t_{d(off)}$	Turn-Off Delay Time			103		ns
t_f	Turn-Off Fall Time			3.4		ns
SOURCE-DRAIN DIODE CHARACTERISTICS						
I_S	Maximum Continuous Source to Drain Diode Forward Current				65	A
I_{SM}	Maximum Pulsed Source to Drain Diode Forward Current				162.5	A
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_{SD} = 32.5 A			1.3	V
t_{rr}	Reverse Recovery Time	V_{DD} = 400 V, I_{SD} = 32.5 A, dI_F/dt = 100 A/μs		137		ns
Q_{rr}	Reverse Recovery Charge			792		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

TYPICAL CHARACTERISTICS

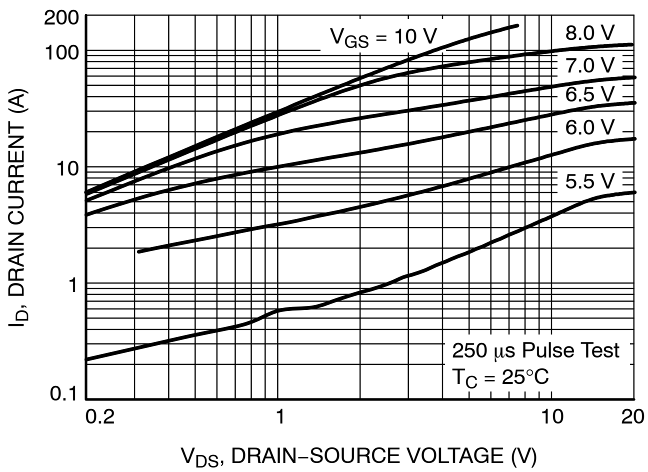


Figure 1. On−Region Characteristics

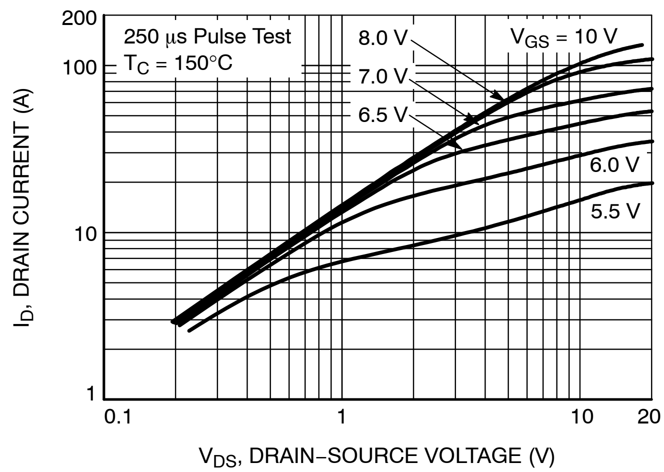


Figure 2. On−Region Characteristics

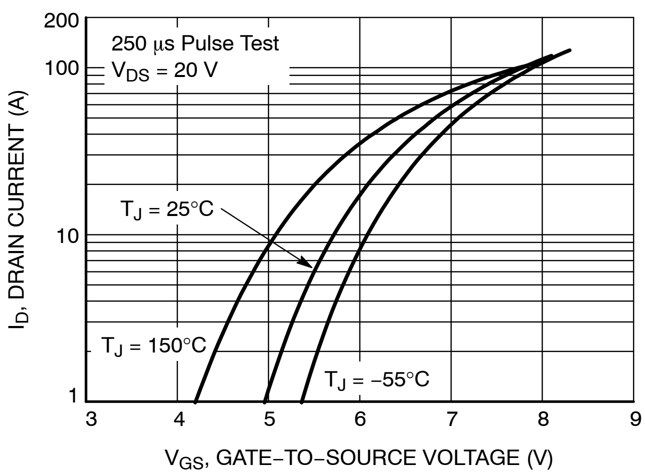


Figure 3. Transfer Characteristics

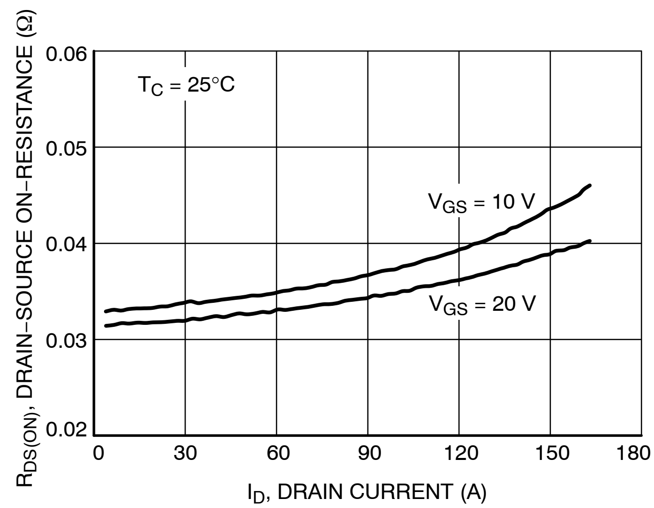


Figure 4. On−Resistance Variation vs. Drain Current and Gate Voltage

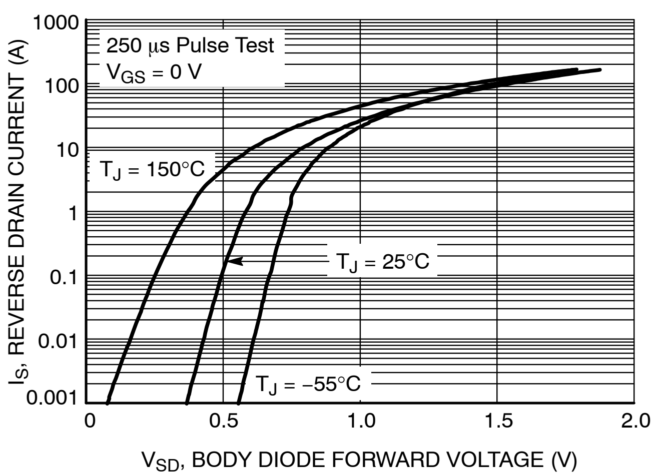


Figure 5. Body Diode Forward Voltage Variation vs. Source Current and Temperature

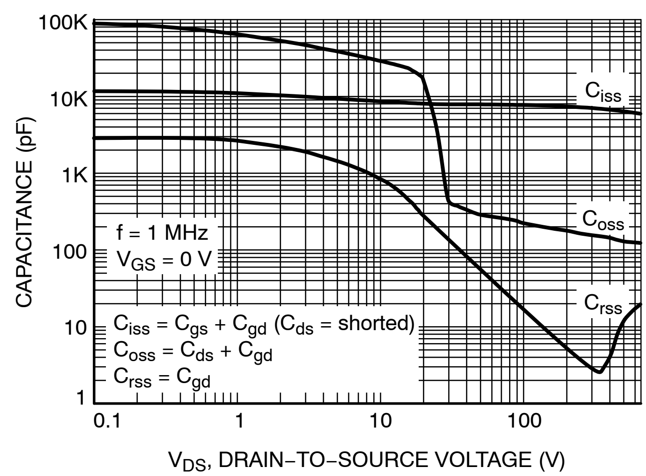


Figure 6. Capacitance Characteristics

TYPICAL CHARACTERISTICS

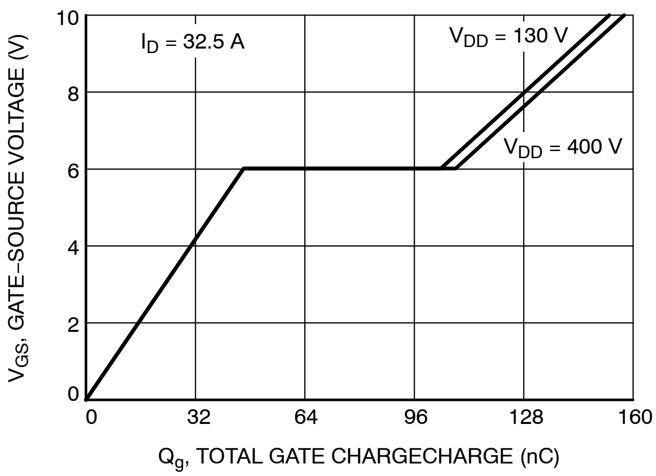


Figure 7. Gate Charge Characteristics

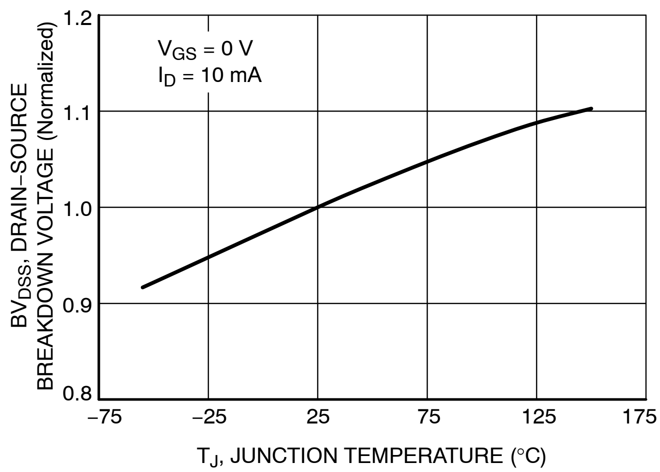


Figure 8. Breakdown Voltage Variation vs. Temperature

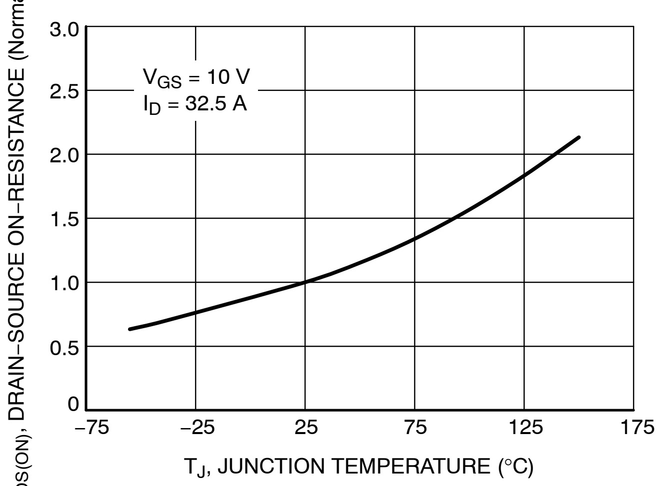


Figure 9. On−Resistance Variation vs. Temperature

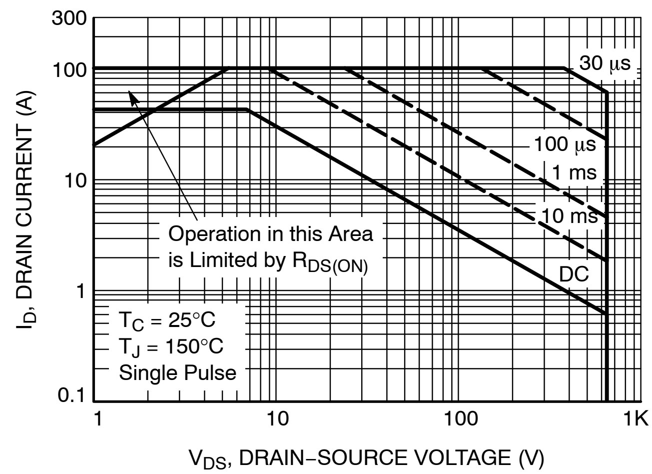


Figure 10. Maximum Safe Operating Area

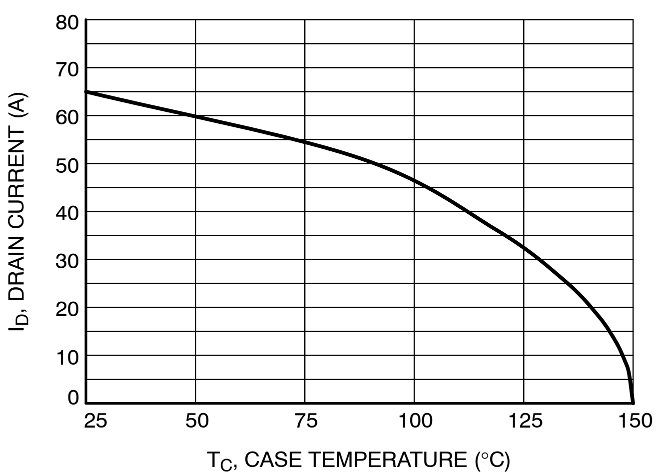


Figure 11. Maximum Drain Current vs. Case Temperature

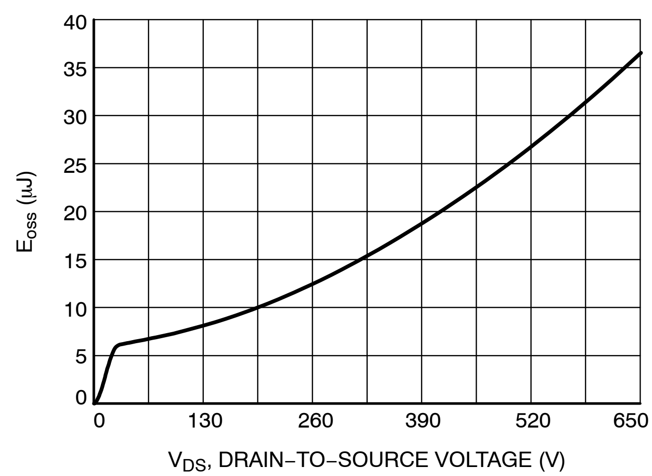


Figure 12. EOSS vs. Drain−to−Source Voltage

TYPICAL CHARACTERISTICS

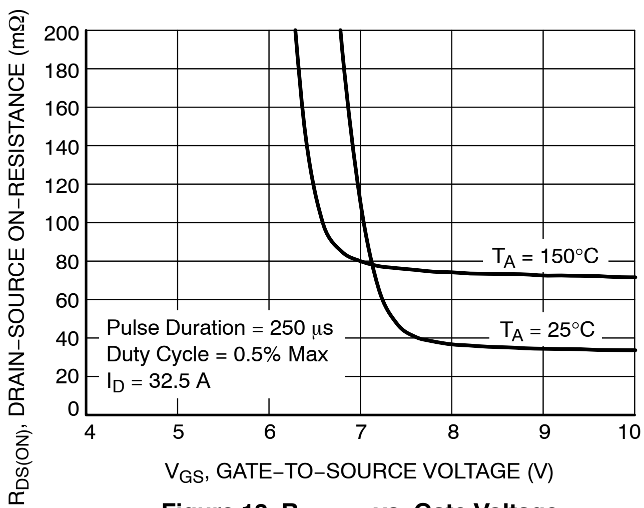


Figure 13. $R_{DS(ON)}$ vs. Gate Voltage

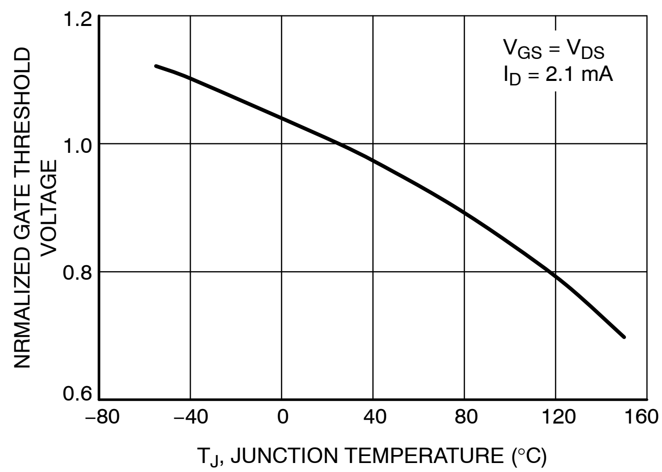
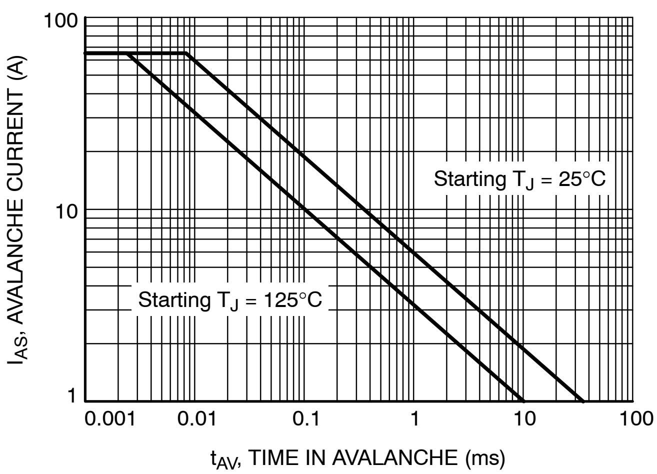


Figure 14. Normalized Gate Threshold Voltage vs. Temperature



If R = 0
t_{AV} = (L)(I_{AS})/(1.3*RATED BV_{DSS} − V_{DD})
If R ≠ 0
t_{AV} = (L/R)In[(I_{AS}*R)/(1.3*RATED BV_{DSS} − V_{DD}) +1]

NOTE: Refer to Application Notes AN7514 and AN7515

Figure 15. Unclamped Inductive Switching Capability

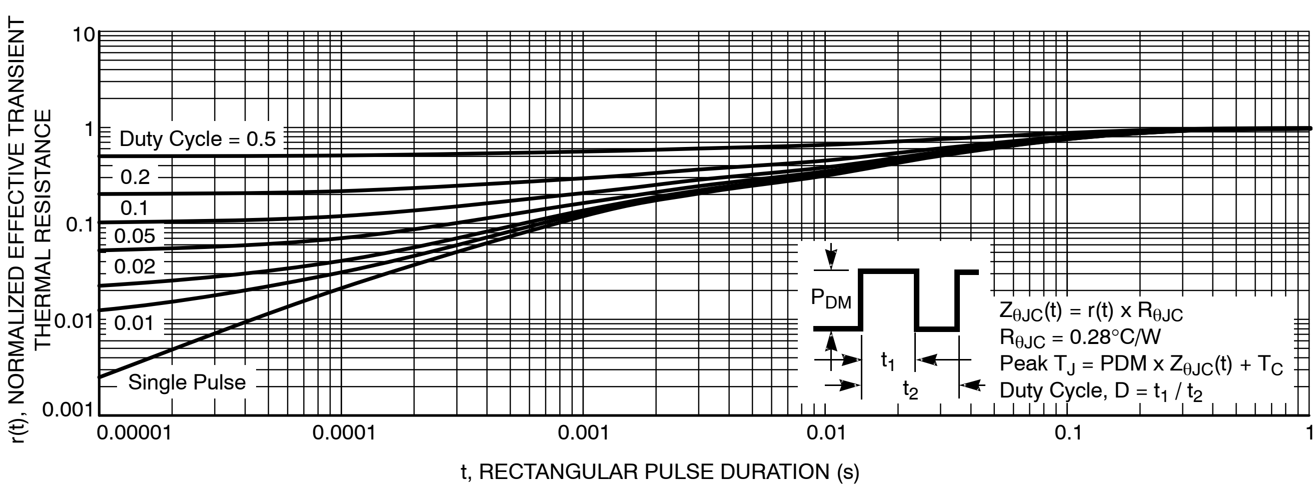


Figure 16. Transient Thermal Response Curve

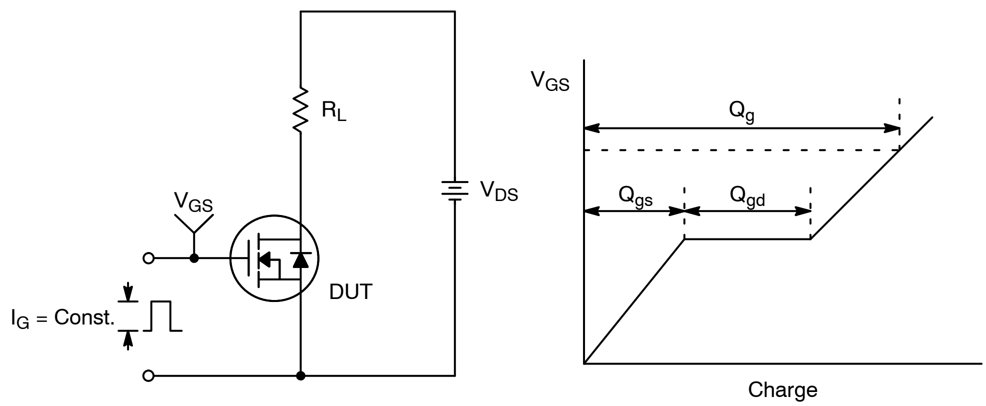


Figure 17. Gate Charge Test Circuit & Waveform

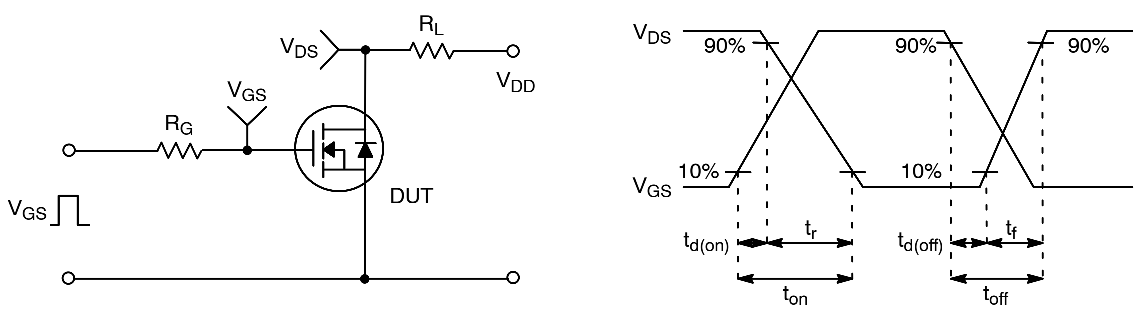


Figure 18. Resistive Switching Test Circuit & Waveforms

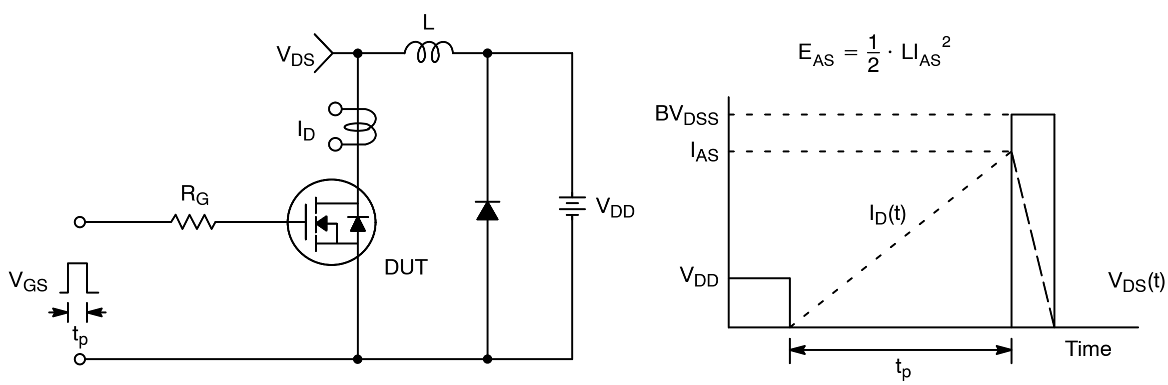


Figure 19. Unclamped Inductive Switching Test Circuit & Waveforms

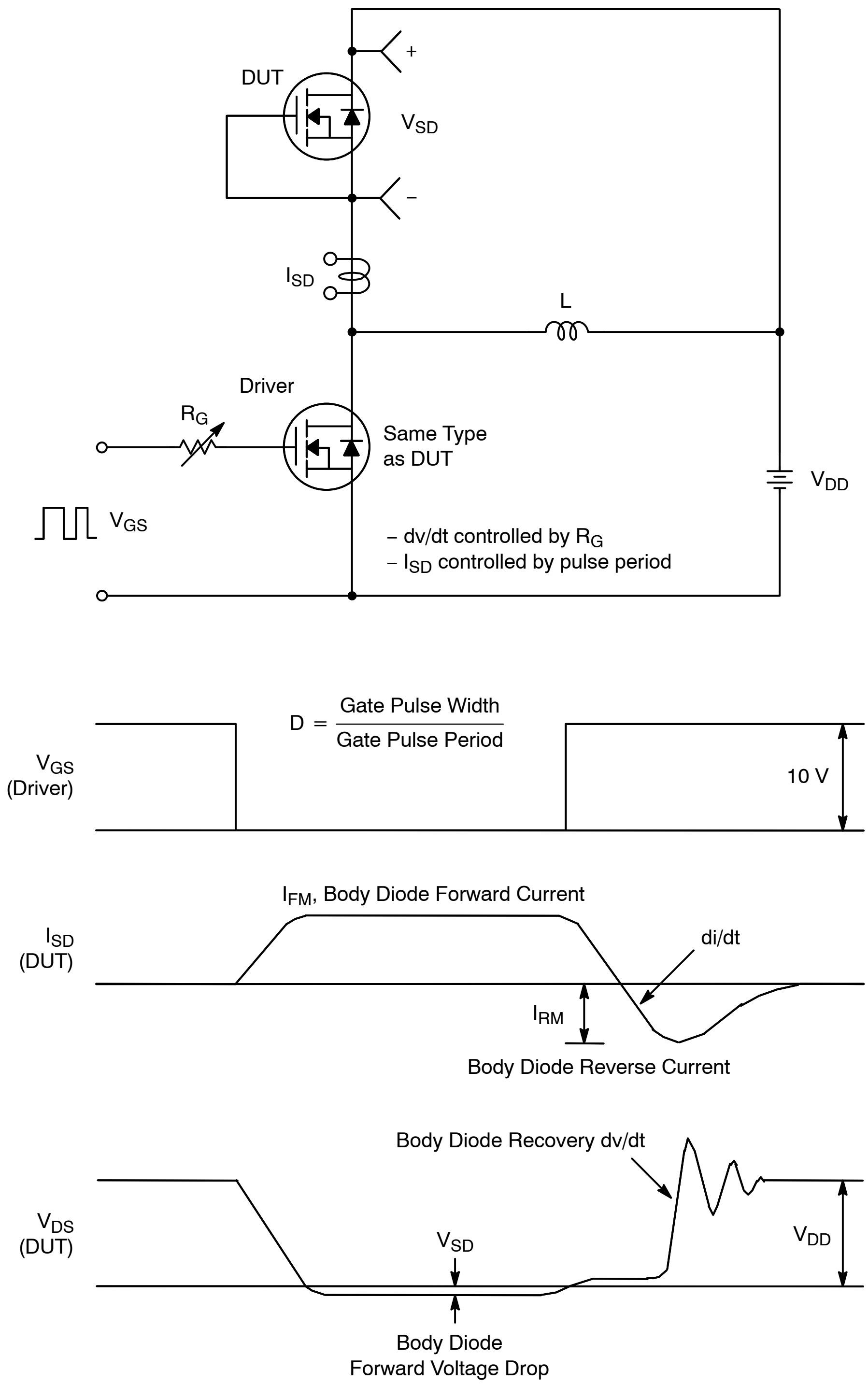
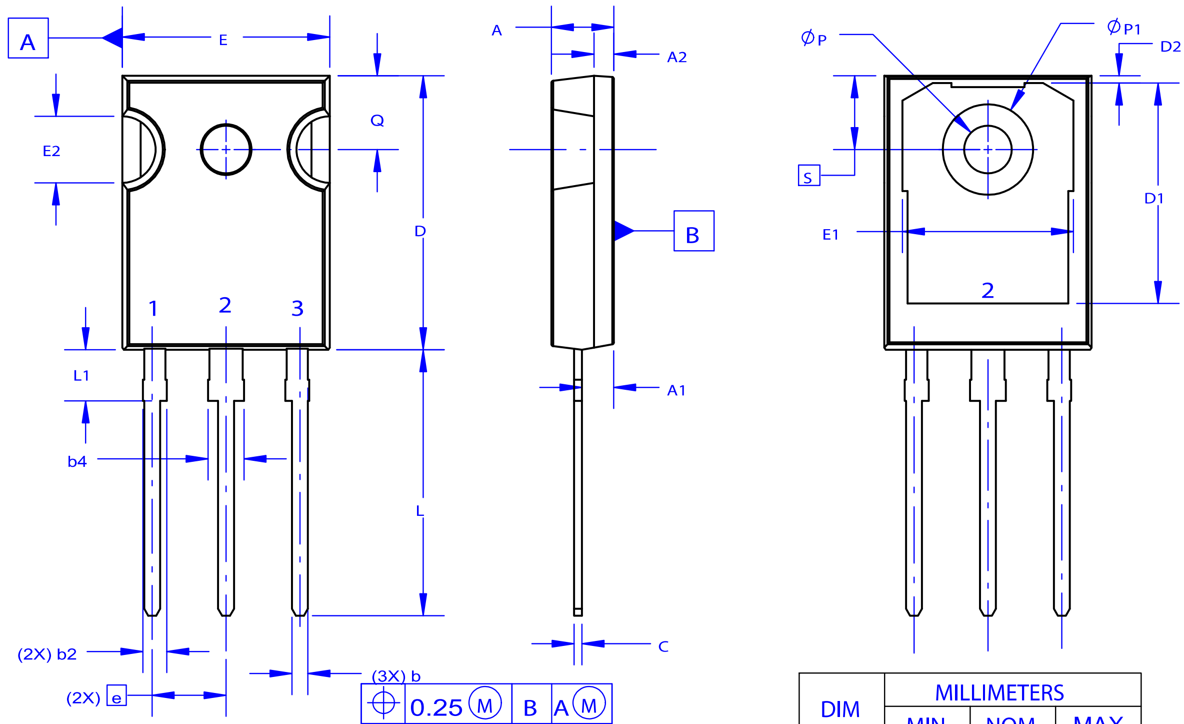


Figure 20. Peak Diode Recovery dv/dt Test Circuit & Waveforms

PACKAGE DIMENSIONS

TO−247−3LD
CASE 340CX
ISSUE A



NOTES: UNLESS OTHERWISE SPECIFIED.

A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
B. ALL DIMENSIONS ARE IN MILLIMETERS.
C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.96	5.08	5.20
e	~	5.56	~
L	19.75	20.00	20.25
L1	3.69	3.81	3.93
ØP	3.51	3.58	3.65
Q	5.34	5.46	5.58
S	5.34	5.46	5.58
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D1	13.08	~	~
D2	0.51	0.93	1.35
E1	12.81	~	~
ØP1	6.60	6.80	7.00

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT
North American Technical Support:
Voice Mail: 1 800−282−9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:
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